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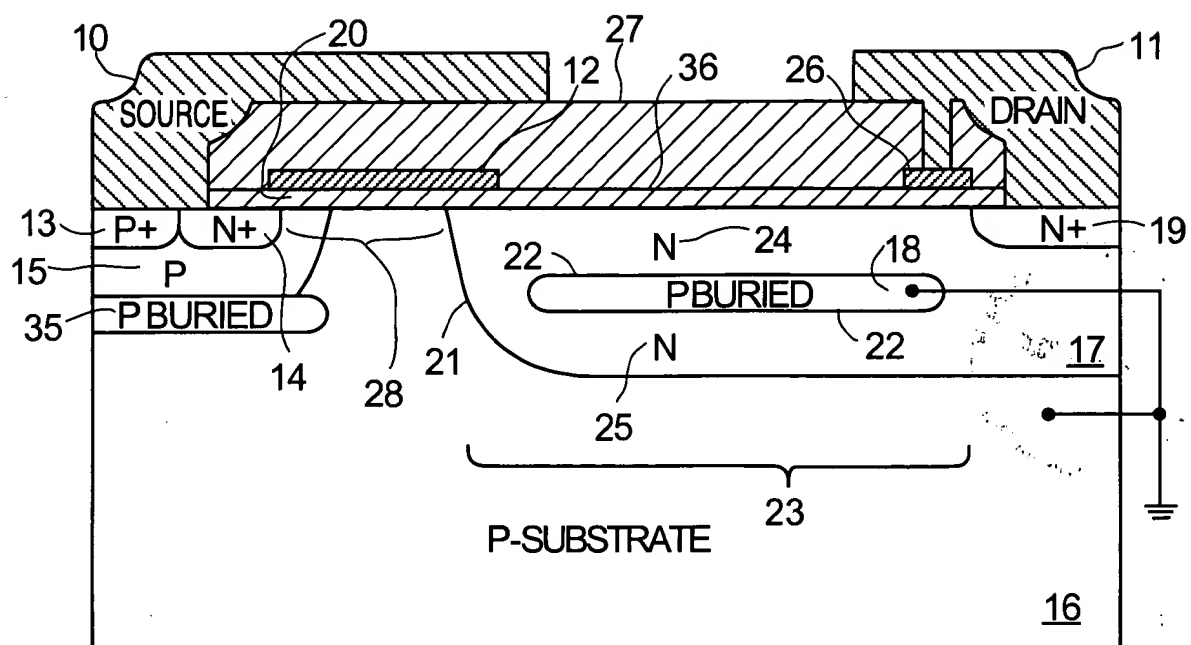


FIG. 1

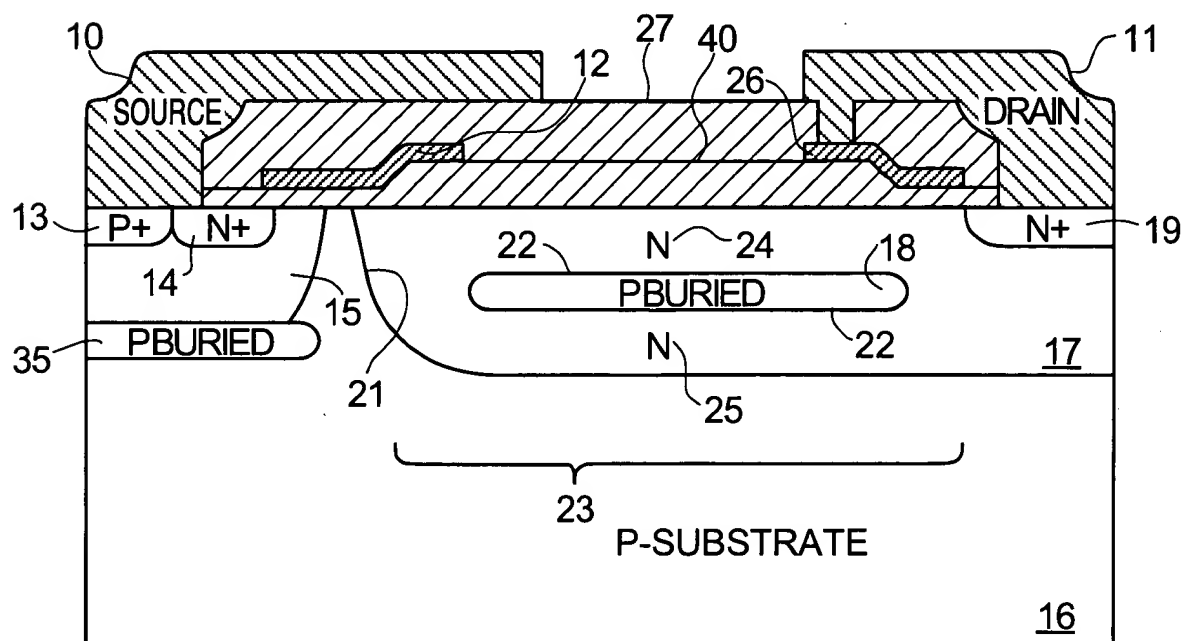


FIG. 2

This diagram shows a cross-sectional view of a semiconductor device. The structure is built on a P-SUBSTRATE 16. A multi-layered gate stack is formed on the substrate, consisting of a GATE OXIDE 36, a POLY GATE 12, and a SOURCE METAL 10. A DRAIN METAL 11 is also present. A POLY DRAIN FIELDPLATE 45 is located on the left side. The device includes a series of horizontal layers labeled N₁, PB1, N₂, PB2, ..., PB_k, and N_{k+1}, which are collectively labeled as 23. These layers are separated by vertical lines 41. A region 19 is indicated on the left, and a region 15 is indicated on the right. The device is also labeled with 13, 14, 17, and 18.

FIG. 3

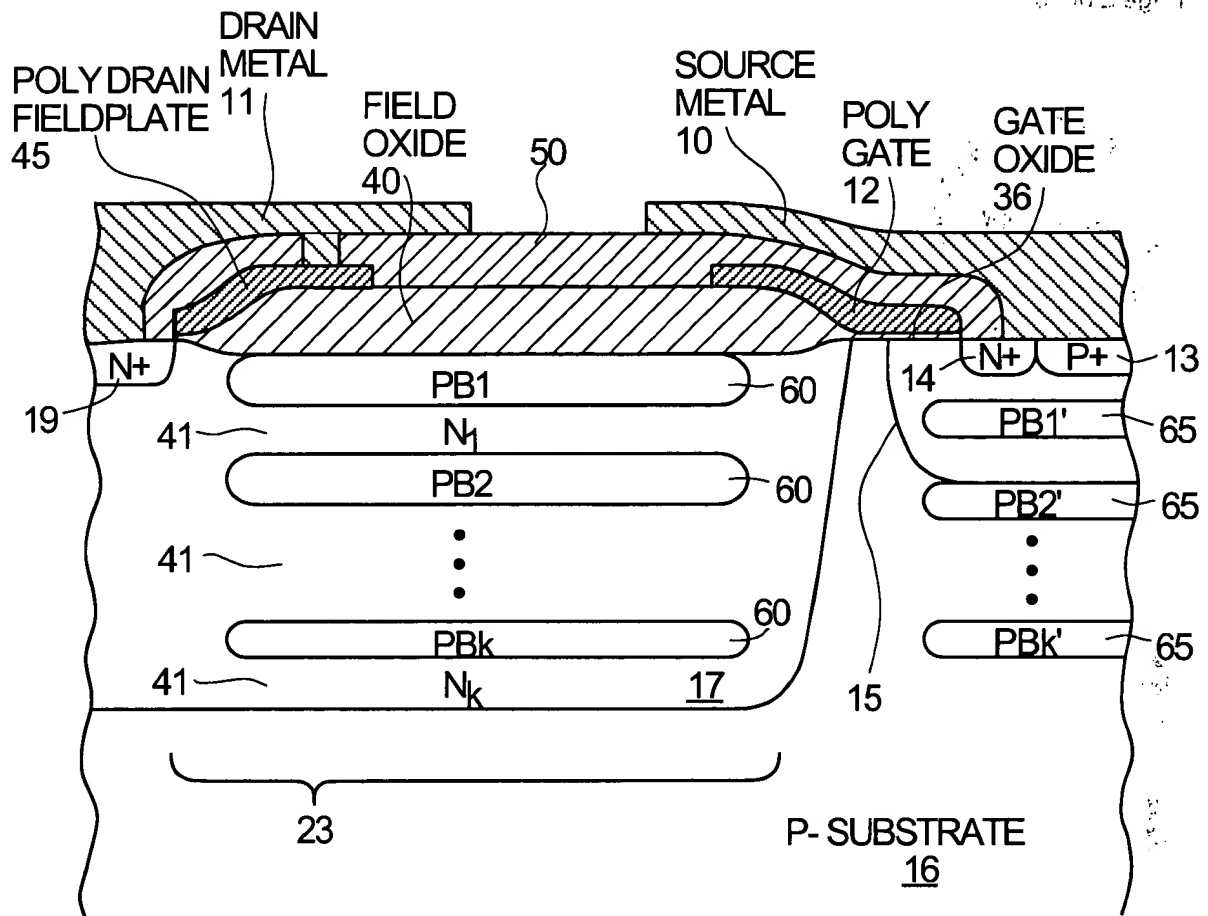


FIG. 4

FIG. 5 is a cross-sectional view of a transistor with a buried channel. The transistor includes a substrate 16, a gate stack 12, a source region 10, and a drain region 11. The gate stack 12 is formed on the substrate 16 and includes a gate dielectric 12 and a gate electrode 26. The source region 10 is formed in the substrate 16 and includes a P+ region 13, an N+ region 14, and a P region 110. The drain region 11 is formed in the substrate 16 and includes an N+ region 19. A buried channel region 18 is formed in the substrate 16, extending from the source region 10 to the drain region 11. The buried channel region 18 is formed in a P region 106 of the substrate 16. A P+ region 28 is formed in the substrate 16, adjacent to the source region 10. A P region 35 is formed in the substrate 16, adjacent to the P+ region 28. A P region 109 is formed in the substrate 16, adjacent to the P region 35. A P region 23 is formed in the substrate 16, adjacent to the P region 109. A P region 106 is formed in the substrate 16, adjacent to the P region 23. A P region 106 is formed in the substrate 16, adjacent to the P region 23.

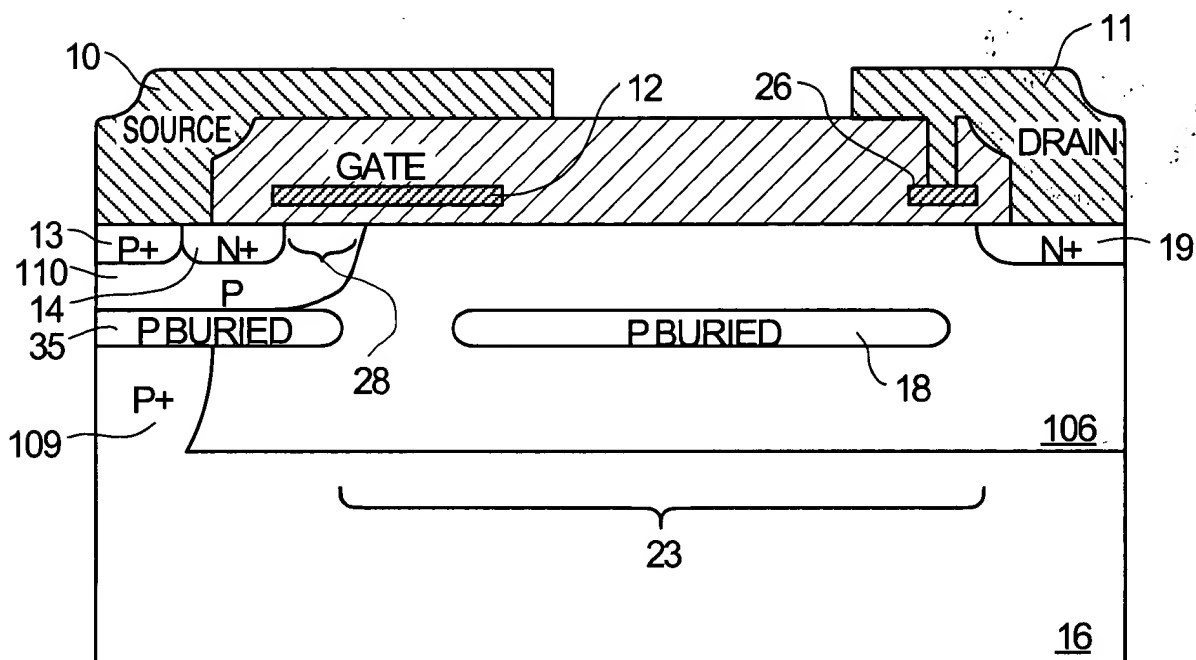


FIG. 5

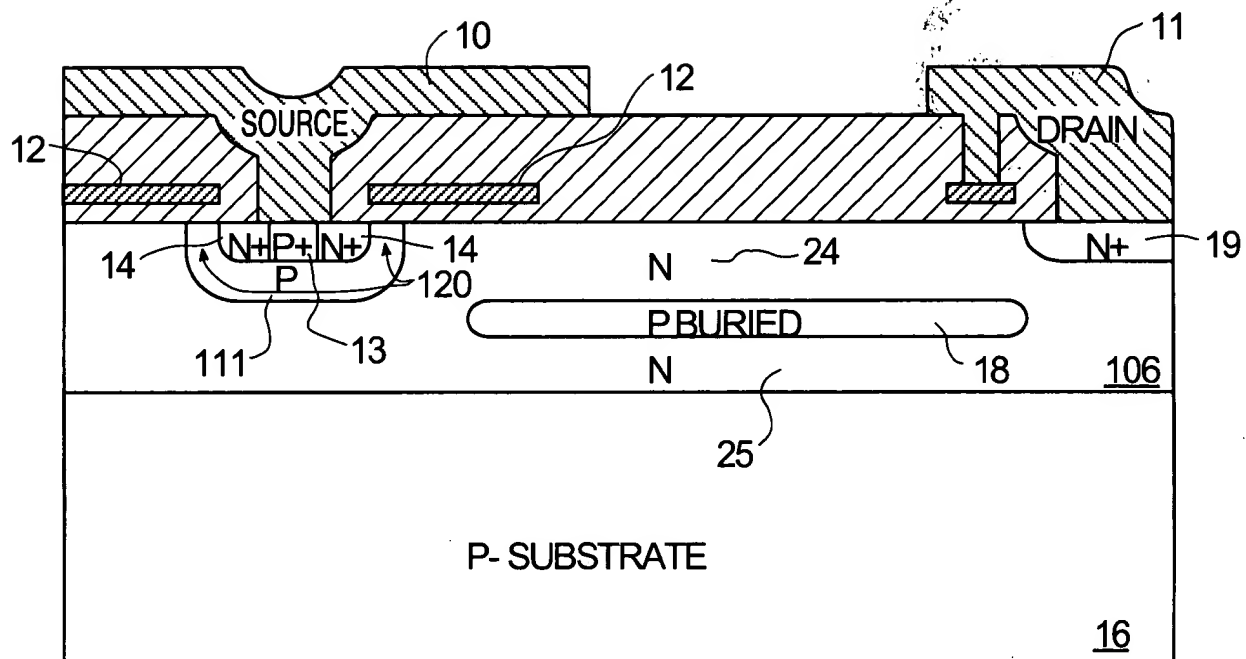
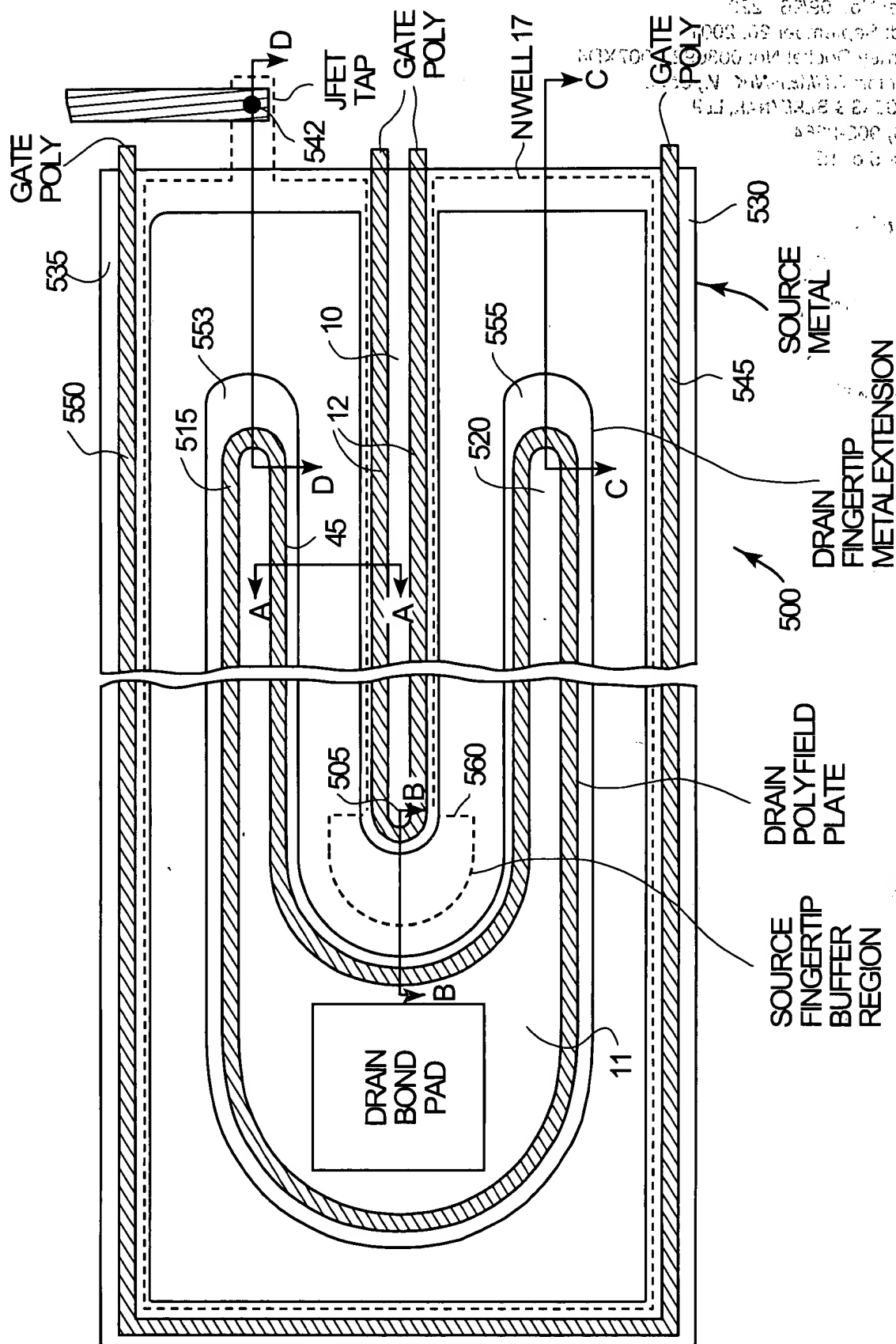


FIG. 6



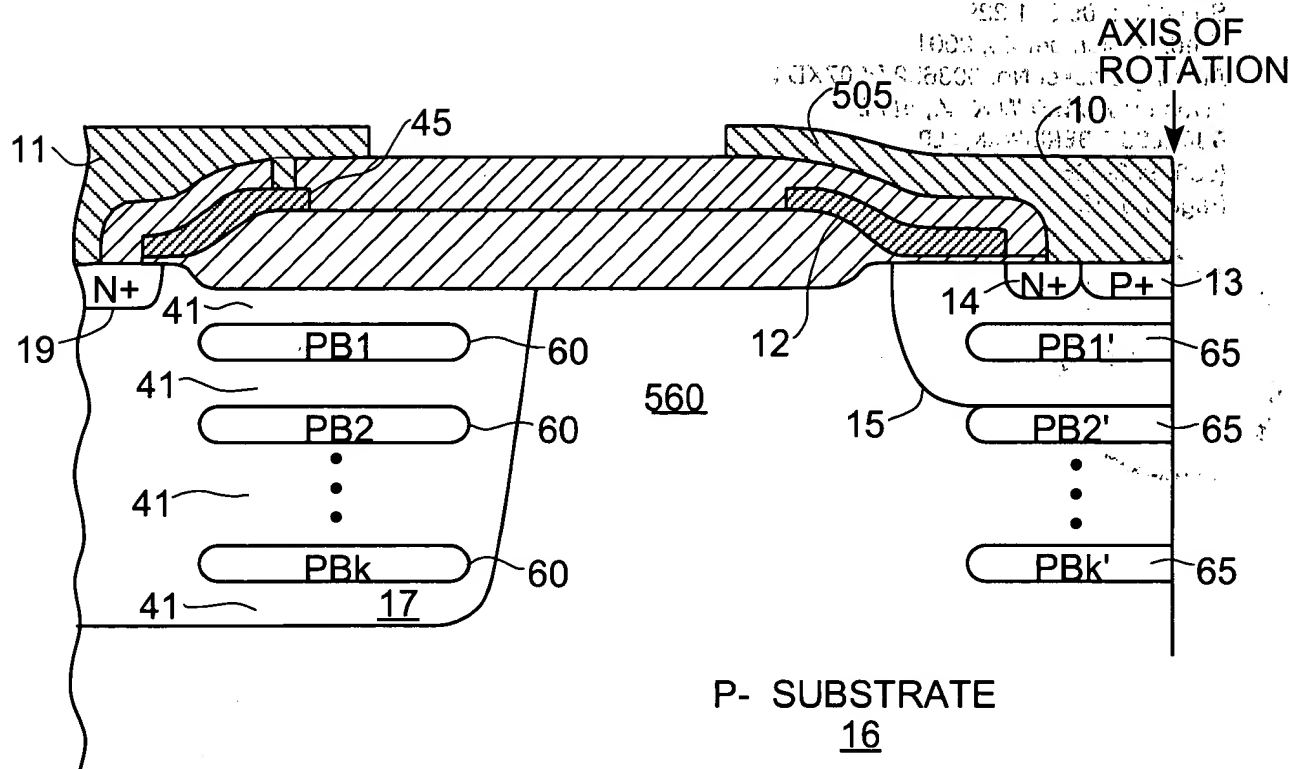


FIG. 8

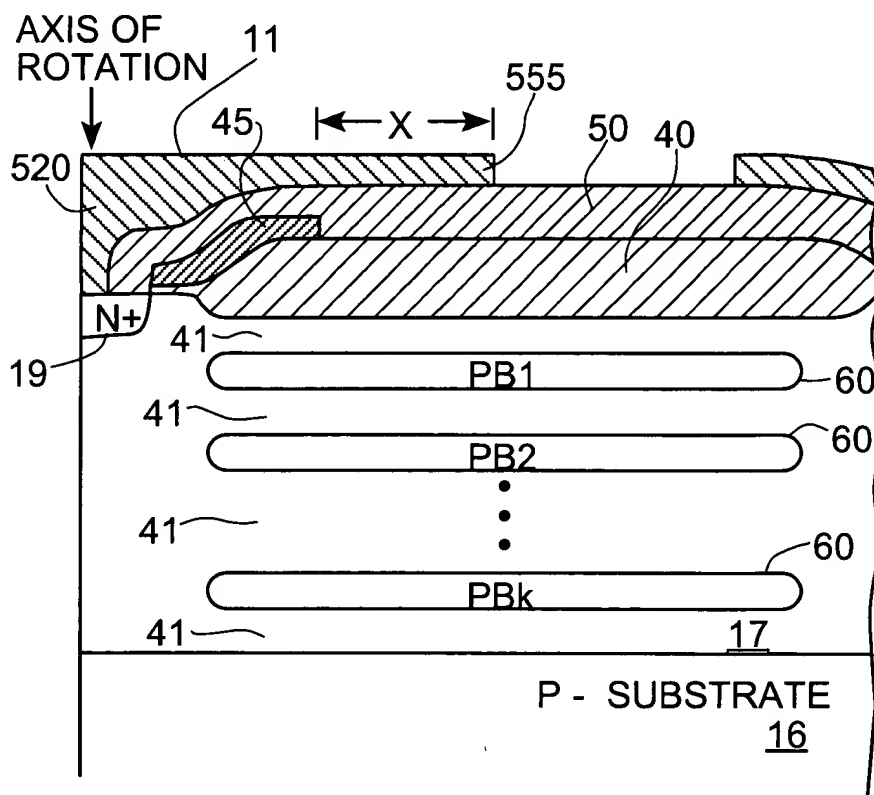


FIG. 9

[illegible]

FIG. 10

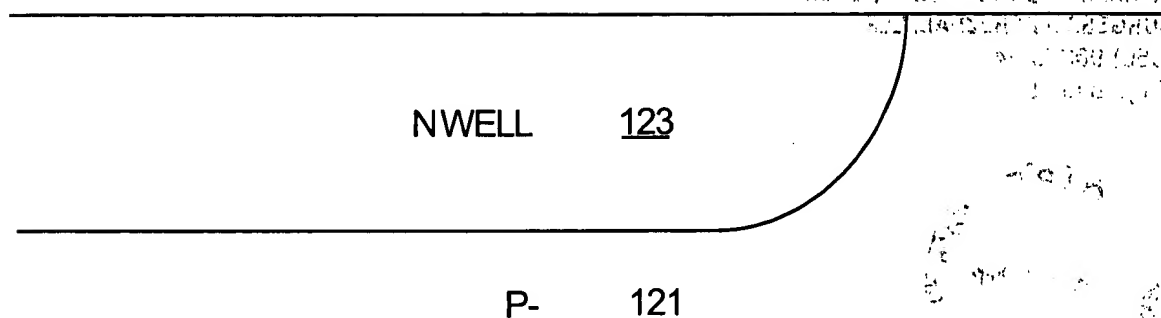


FIG. 11a

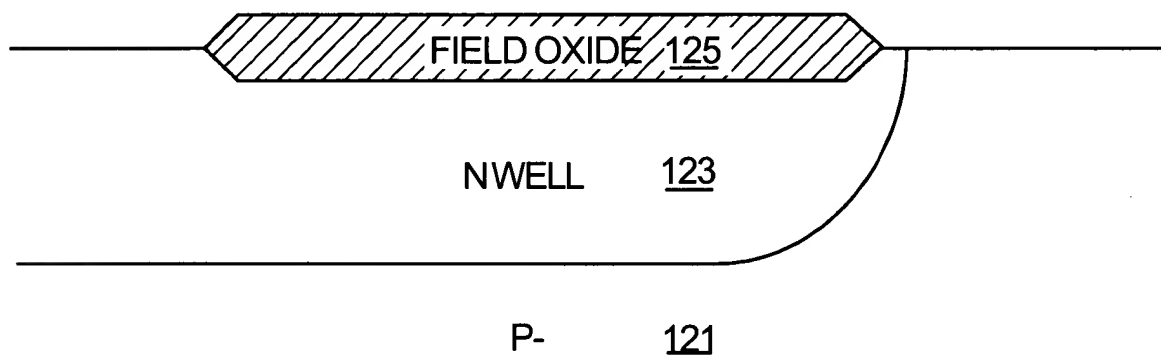


FIG. 11b

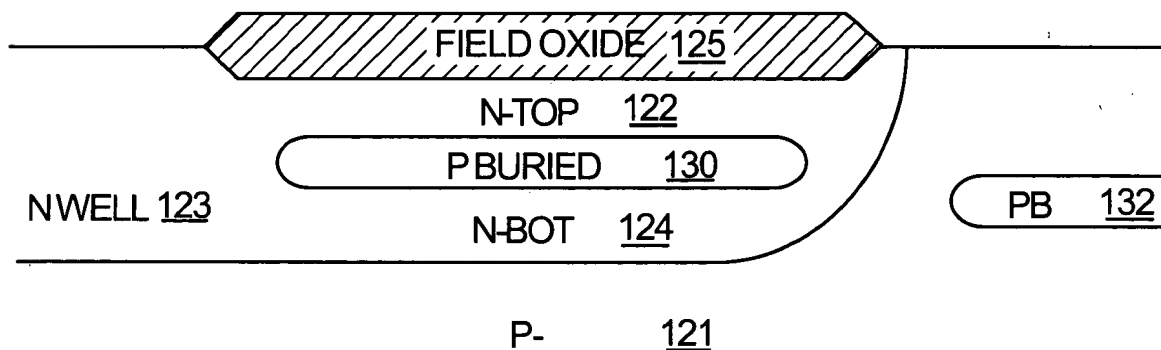


FIG. 11c

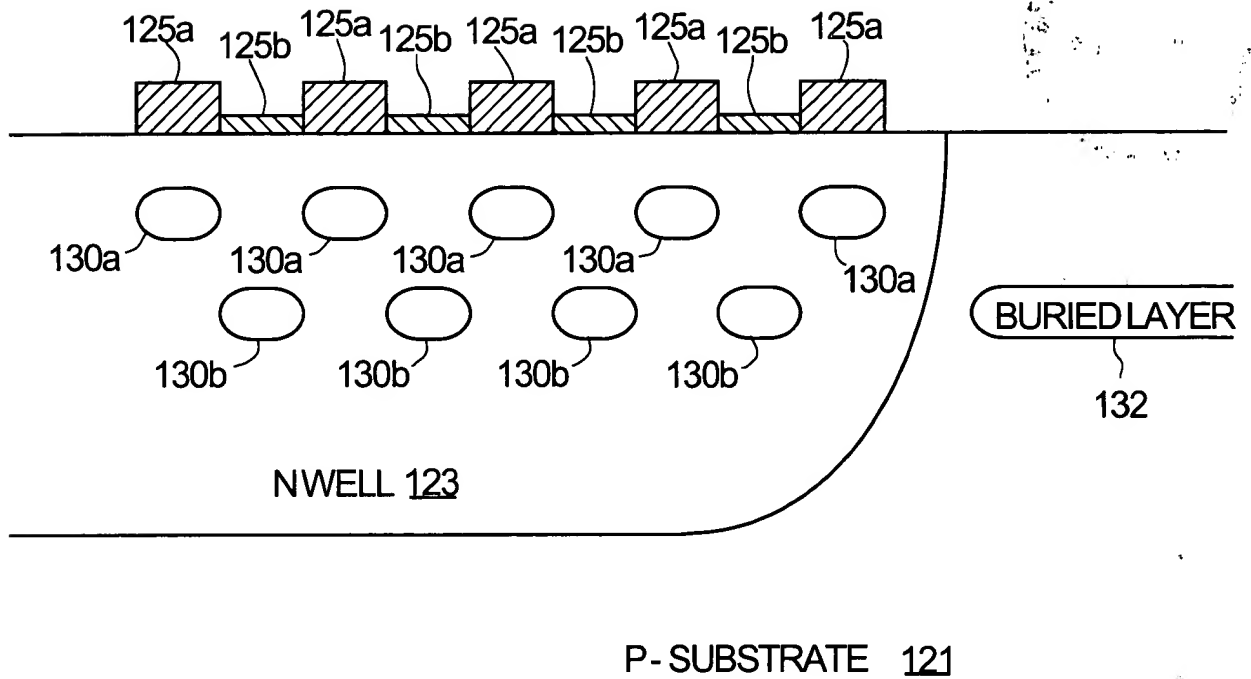


FIG. 11d

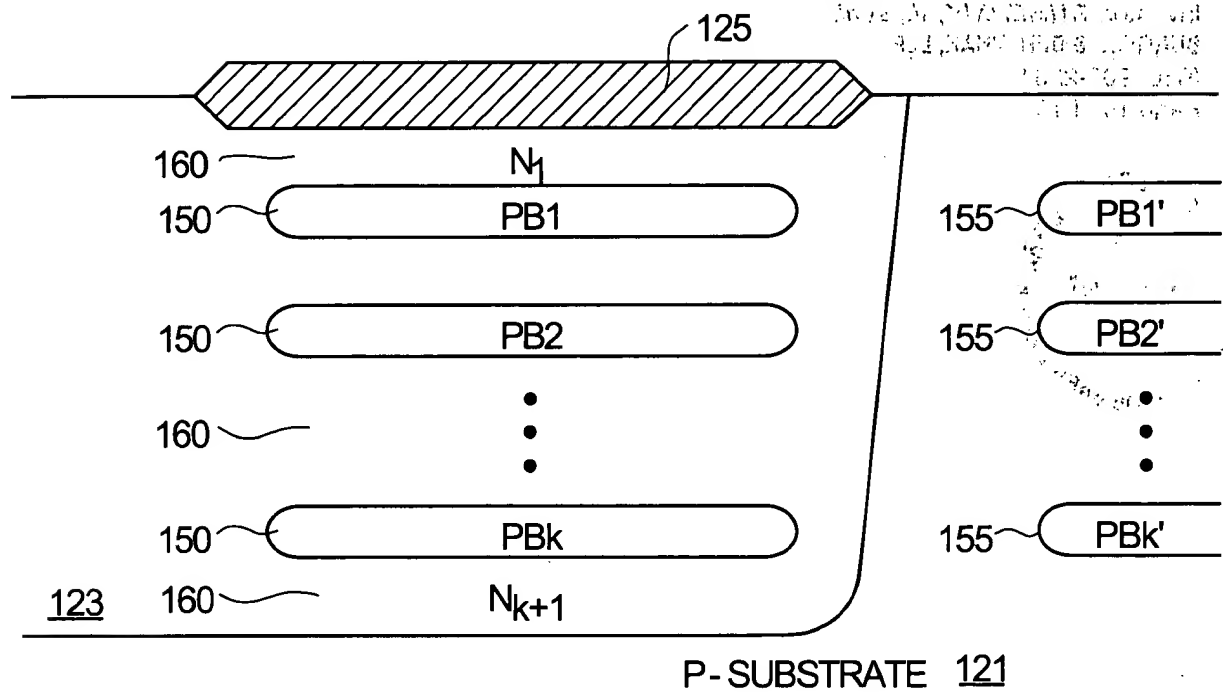


FIG. 11e

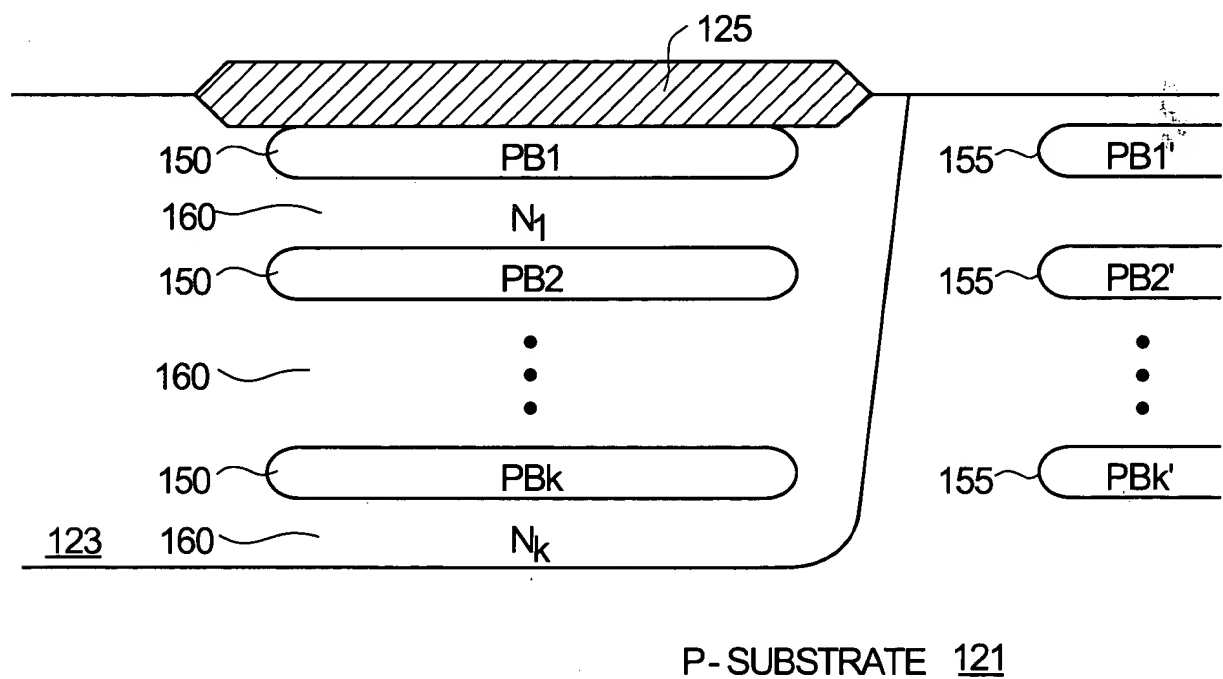


FIG. 11f

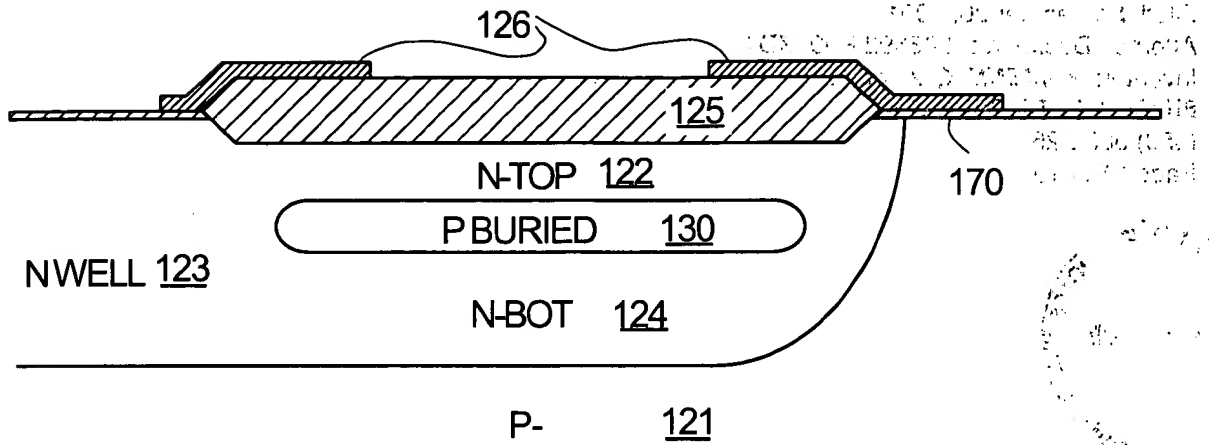


FIG. 11g

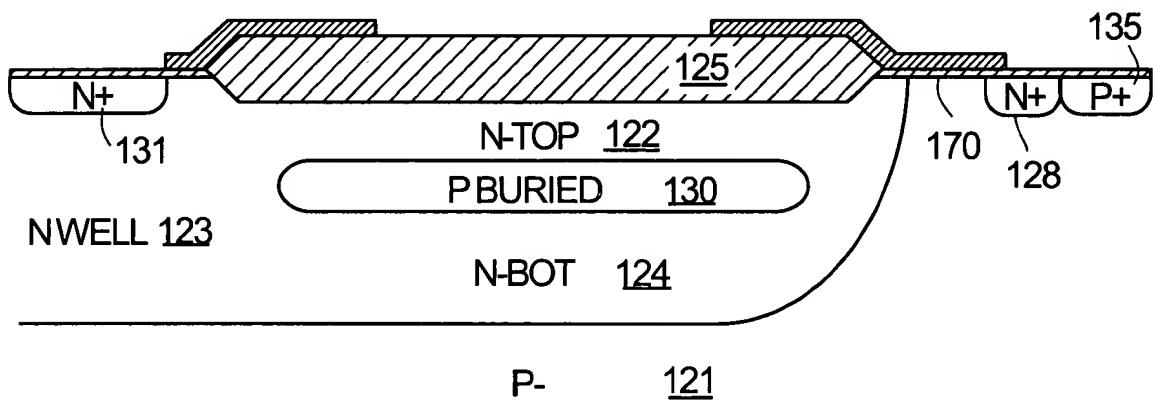


FIG. 11h

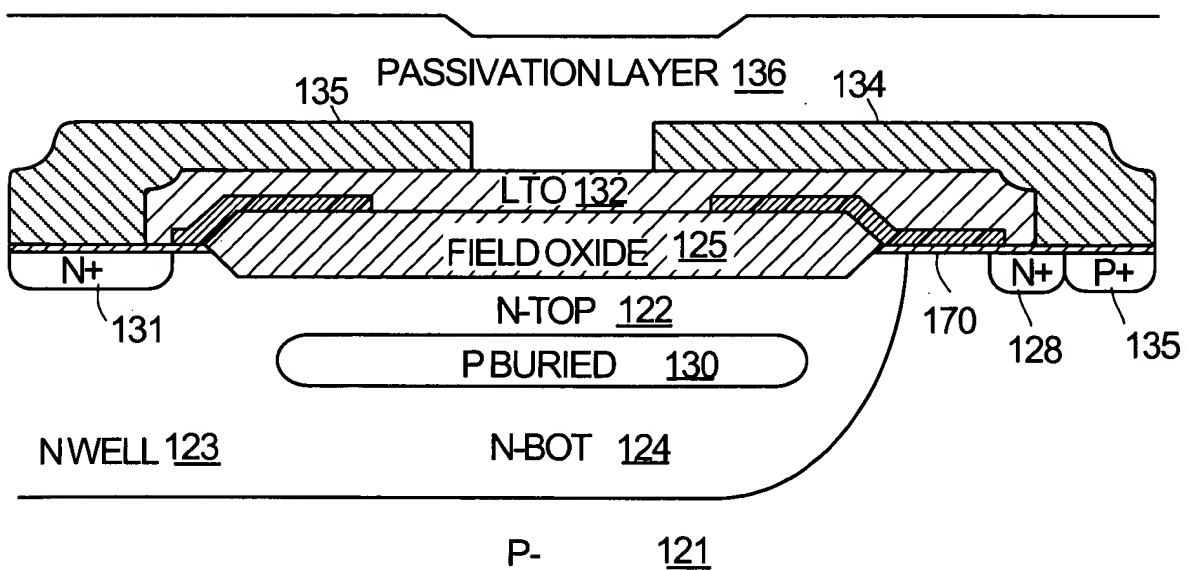


FIG. 11i

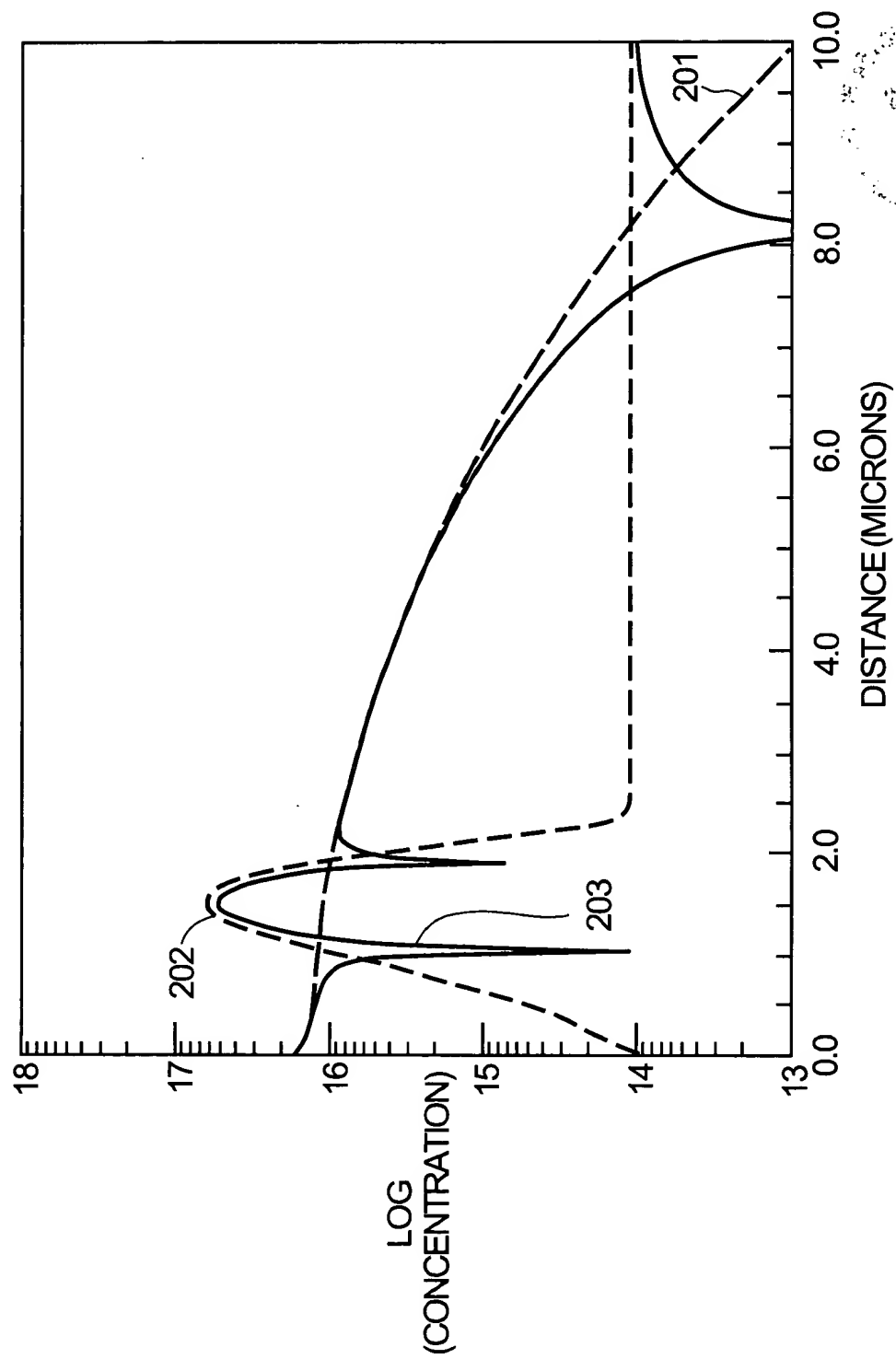


FIG. 12

1. *Chlorophyll a* (Chl *a*)





FIG. 14